## ATS-CVD Series PECVD-PVD Cluster System for Graphene Synthesis



## Special Features

## Specifications

- Multi-functional cluster system combined with PECVD, sputter and E-beam evaporation for high quality graphene synthesis
- Maximum substrate heater temperature: $1,000^{\circ} \mathrm{C}$ for PECVD, $800^{\circ} \mathrm{C}$ for Sputter and $500^{\circ} \mathrm{C}$ for e-beam evaporation, respectively
- Automatic loading transfer chamber around which PECVD, Sputter and E-beam evaporation chambers are attached
- PC controled system : recipe save, open function, and fully automation except for e-beam evaporation module
- Wafer capacity: 8" x1

| PECVD |  |
| :---: | :---: |
| Item | Specifications |
| Source power | $2.5 \mathrm{~kW}(13.56 \mathrm{MHz})$ |
| Bias power | $0.3 \mathrm{~kW}(12.56 \mathrm{MHz})$ |
| TMP | 1,100l/sec |
| Dry pump | 9,000 $/ \mathrm{min}$ |
| Substrate heater | SiC coated graphite, Max. $1,000{ }^{\circ} \mathrm{C}$ |
| RF ICP coil | 2turns |
| MFC | CH4(50sccm), H2(200sccm), Ar(200sccm) |
| Pressure control | Automatic pressure control system |

- Average throughput: 2,000 wafer/year

| Sputter |  | E-beam evaporation |  |
| :---: | :---: | :---: | :---: |
| Item | Specifications | ltem | Specifications |
| Sputter power | 1.5 kW (DC) | E-beam power | 10kW(10kV, 1A) |
| Bias power | 0.3kW (13.56MHz) |  |  |
| TMP | 1,100 $/$ sec |  |  |
| Dry pump | 9,000 $/$ min | TMP | 1,100 $/$ sec |
| Substrate heater | SiC coated graphite, Max. $800^{\circ} \mathrm{C}$ | Dry pump | 9,000 $/$ min |
| MFC | $\operatorname{Ar}(100 \mathrm{sccm}), \mathrm{O} 2(50 \mathrm{sccm})$, $\mathrm{N} 2(50 \mathrm{sccm})$ | Substrate heater | SiC coated graphite, Max. $500{ }^{\circ} \mathrm{C}$ |
| Pressure control | Automatic pressure control system | Thickness monitor | SQC310 |



Crystal structures of different carbon allotropes


Raman spectra of synthesized graphene film on 100 nm PdCo film and 300 nm Ni film on $\mathrm{SiO}_{2}$ substrate at different temperatures


Schematic illustration for transfer-free growth of graphene on a substrate

## Layout



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